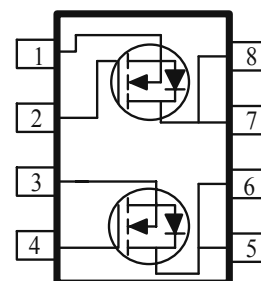
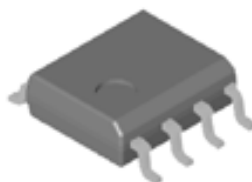


## Dual N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low  $r_{DS(on)}$  Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Low side high current DC-DC Converter applications



| PRODUCT SUMMARY |                            |           |
|-----------------|----------------------------|-----------|
| $V_{DS}$ (V)    | $r_{DS(on)}$ m( $\Omega$ ) | $I_D$ (A) |
| 30              | 34 @ $V_{GS} = 10V$        | 6.9       |
|                 | 41 @ $V_{GS} = 4.5V$       | 6.0       |

| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED) |                          |                |            |                  |
|-----------------------------------------------------------------------------|--------------------------|----------------|------------|------------------|
| Parameter                                                                   |                          | Symbol         | Limit      | Units            |
| Drain-Source Voltage                                                        |                          | $V_{DS}$       | 30         | V                |
| Gate-Source Voltage                                                         |                          | $V_{GS}$       | $\pm 20$   |                  |
| Continuous Drain Current <sup>a</sup>                                       | $T_A = 25^\circ\text{C}$ | $I_D$          | $\pm 6.9$  | A                |
|                                                                             | $T_A = 70^\circ\text{C}$ |                | $\pm 5.6$  |                  |
| Pulsed Drain Current <sup>b</sup>                                           |                          | $I_{DM}$       | $\pm 40$   |                  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>                   |                          | $I_S$          | 1.7        | A                |
| Power Dissipation <sup>a</sup>                                              | $T_A = 25^\circ\text{C}$ | $P_D$          | 2.1        | W                |
|                                                                             | $T_A = 70^\circ\text{C}$ |                | 1.3        |                  |
| Operating Junction and Storage Temperature Range                            |                          | $T_J, T_{stg}$ | -55 to 150 | $^\circ\text{C}$ |

| THERMAL RESISTANCE RATINGS               |                         |                 |         |                    |
|------------------------------------------|-------------------------|-----------------|---------|--------------------|
| Parameter                                |                         | Symbol          | Maximum | Units              |
| Maximum Junction-to-Ambient <sup>a</sup> | $t \leq 10 \text{ sec}$ | $R_{\theta JA}$ | 62.5    | $^\circ\text{C/W}$ |
|                                          | Steady-State            |                 | 110     | $^\circ\text{C/W}$ |

### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

| SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED) |                     |                                                                                                  |        |      |      |      |
|---------------------------------------------------------------|---------------------|--------------------------------------------------------------------------------------------------|--------|------|------|------|
| Parameter                                                     | Symbol              | Test Conditions                                                                                  | Limits |      |      | Unit |
|                                                               |                     |                                                                                                  | Min    | Typ  | Max  |      |
| Static                                                        |                     |                                                                                                  |        |      |      |      |
| Gate-Threshold Voltage                                        | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 uA                                      | 1      |      |      |      |
| Gate-Body Leakage                                             | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                  |        |      | ±100 | nA   |
| Zero Gate Voltage Drain Current                               | I <sub>DSS</sub>    | V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V                                                    |        |      | 1    | uA   |
|                                                               |                     | V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C                             |        |      | 10   |      |
| On-State Drain Current <sup>A</sup>                           | I <sub>D(on)</sub>  | V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V                                                    | 20     |      |      | A    |
| Drain-Source On-Resistance <sup>A</sup>                       | r <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.9 A                                                   |        |      | 34   | mΩ   |
|                                                               |                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> =6.0 A                                                   |        |      | 41   |      |
| Forward Tranconductance <sup>A</sup>                          | g <sub>fs</sub>     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 6.9 A                                                   |        | 25   |      | S    |
| Diode Forward Voltage                                         | V <sub>SD</sub>     | I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V                                                    |        | 0.77 |      | V    |
| Dynamic <sup>b</sup>                                          |                     |                                                                                                  |        |      |      |      |
| Total Gate Charge                                             | Q <sub>g</sub>      | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V,<br>I <sub>D</sub> = 6.9 A                       |        | 4.0  |      | nC   |
| Gate-Source Charge                                            | Q <sub>gs</sub>     |                                                                                                  |        | 1.1  |      |      |
| Gate-Drain Charge                                             | Q <sub>gd</sub>     |                                                                                                  |        | 1.4  |      |      |
| Turn-On Delay Time                                            | t <sub>d(on)</sub>  | V <sub>DD</sub> = 15 V, R <sub>L</sub> = 15 Ω , I <sub>D</sub> = 1 A,<br>V <sub>GEN</sub> = 10 V |        | 12   |      | nS   |
| Rise Time                                                     | t <sub>r</sub>      |                                                                                                  |        | 10   |      |      |
| Turn-Off Delay Time                                           | t <sub>d(off)</sub> |                                                                                                  |        | 60   |      |      |
| Fall-Time                                                     | t <sub>f</sub>      |                                                                                                  |        | 15   |      |      |
| Source-Ddrain Reverse Recovery Time                           | t <sub>rr</sub>     | I <sub>F</sub> = 1.7 A, Di/Dt = 100 A/uS                                                         |        | 50   |      |      |

## Notes

- Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

**FREESCALE** reserves the right to make changes without further notice to any products herein. FREESCALE makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does freescale assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in freescale data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. freescale does not convey any license under its patent rights nor the rights of others. freescale products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the freescale product could create a situation where personal injury or death may occur. Should Buyer purchase or use freescale products for any such unintended or unauthorized application, Buyer shall indemnify and hold freescale and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that freescale was negligent regarding the design or manufacture of the part. freescale is an Equal Opportunity/Affirmative Action Employer.

## Typical Electrical Characteristics (N-Channel)

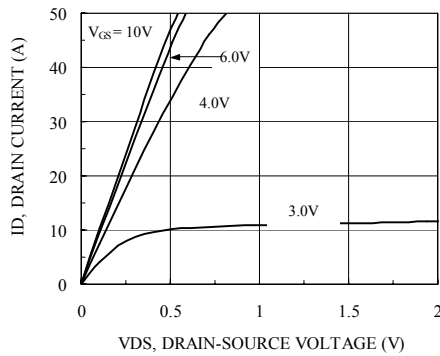


Figure 1. On-Region Characteristics

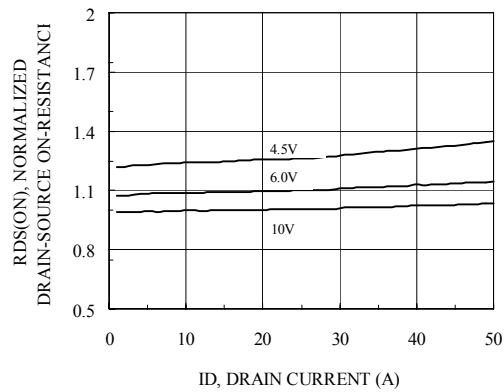


Figure 2. On-Resistance with Drain Current

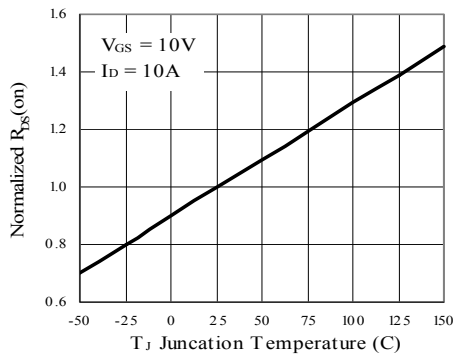


Figure 3. On-Resistance Variation with Temperature

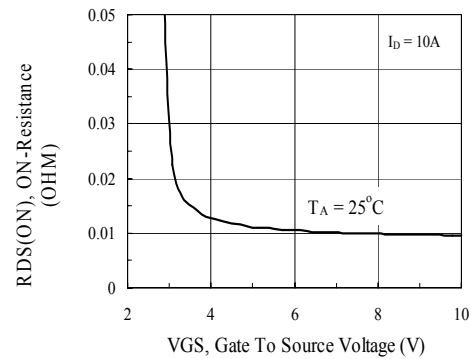


Figure 4. On-Resistance Variation with Gate to Source Voltage

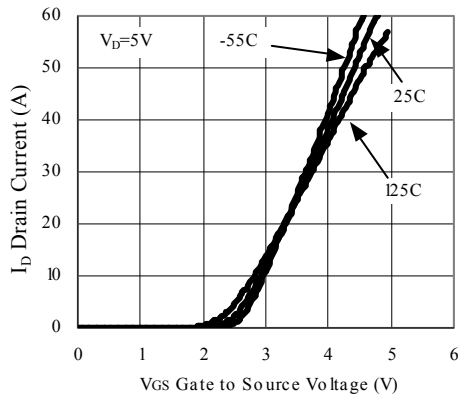


Figure 5. Transfer Characteristics

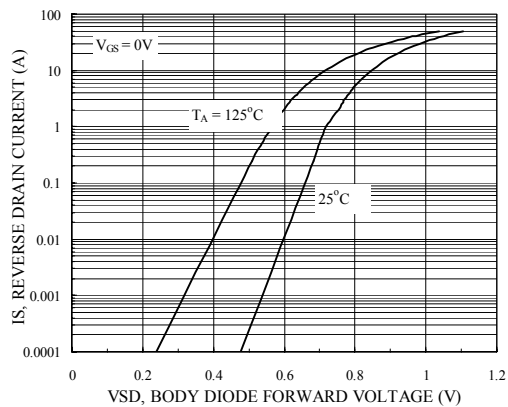


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

## Typical Electrical Characteristics (N-Channel)

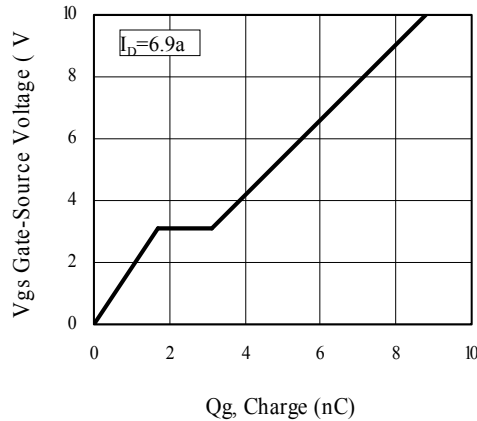


Figure 7. Gate Charge Characteristics

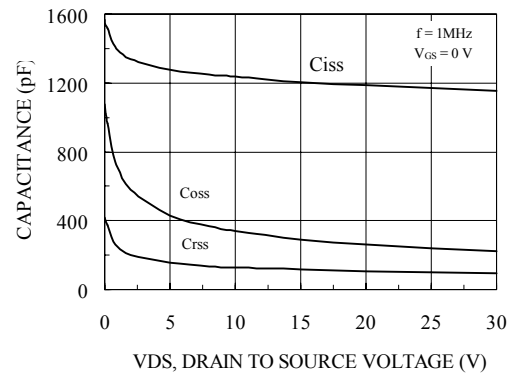


Figure 8. Capacitance Characteristics

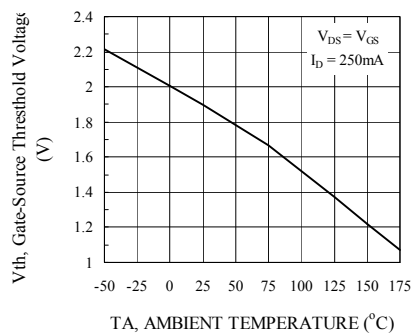


Figure 9. Threshold Vs Ambient Temperature

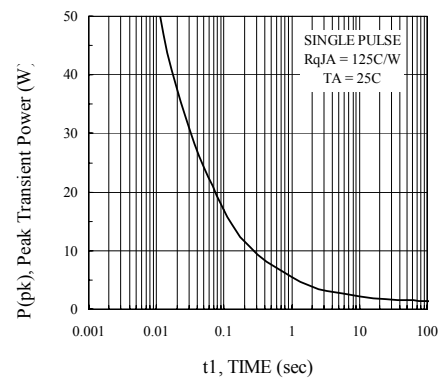


Figure 10. Single Pulse Maximum Power Dissipation

### Normalized Thermal Transient Junction to Ambient

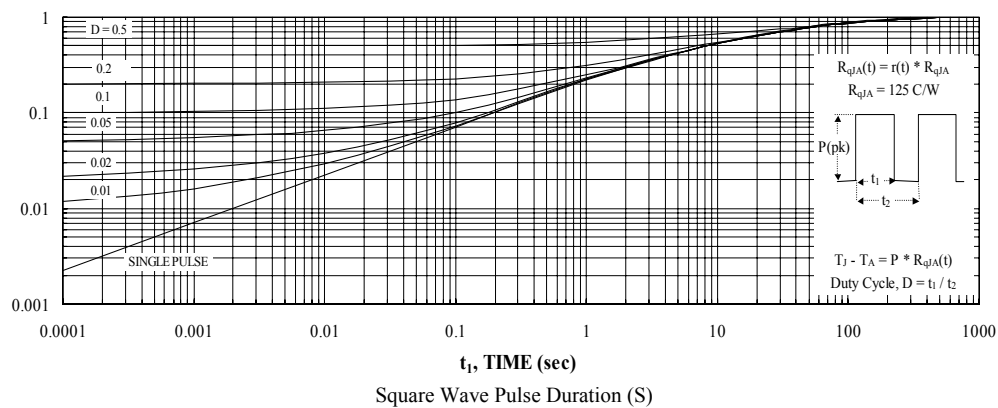
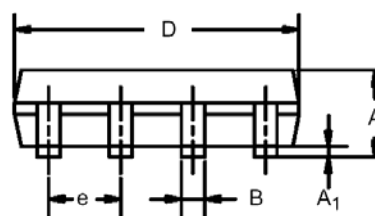
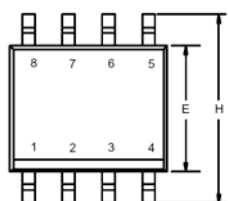


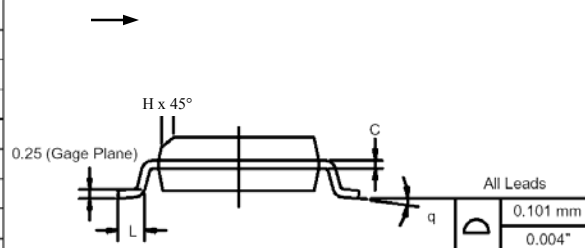
Figure 11. Transient Thermal Response Curve

# Package Information

## SO-8: 8LEAD



| Dim            | MILLIMETERS |      | INCHES    |       |
|----------------|-------------|------|-----------|-------|
|                | Min         | Max  | Min       | Max   |
| A              | 1.35        | 1.75 | 0.053     | 0.069 |
| A <sub>1</sub> | 0.10        | 0.20 | 0.004     | 0.008 |
| B              | 0.35        | 0.51 | 0.014     | 0.020 |
| C              | 0.19        | 0.25 | 0.0075    | 0.010 |
| D              | 4.80        | 5.00 | 0.189     | 0.196 |
| E              | 3.80        | 4.00 | 0.150     | 0.157 |
| e              | 1.27 BSC    |      | 0.050 BSC |       |
| H              | 5.80        | 6.20 | 0.228     | 0.244 |
| h              | 0.25        | 0.50 | 0.010     | 0.020 |
| L              | 0.50        | 0.93 | 0.020     | 0.037 |
| q              | 0°          | 8°   | 0°        | 8°    |



# Ordering information

- AM4920N-T1-XX
  - A: Analog Power
  - M: MOSFET
  - 4920: Part number
  - N: N-Channel
  - T1: Tape & reel
  - XX: Blank: Standard  
PF: Leadfree